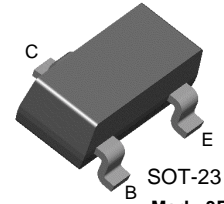


MMBTH10RG

NPN RF Transistor

- This device is designed for use in low noise UHF/VHF amplifiers, with collector currents in the 100 μ A to 20 mA range in common emitter or common base mode of operations, and in low frequency drift, high output UHF oscillators.
- Sourced from process 42.



SOT-23
Mark: 3E
1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current - Continuous	50	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	$^\circ\text{C}$

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These rating are based on a maximum junction temperature of 150 degrees C.
- These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage *	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \mu\text{A}, I_C = 0$	4.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		100	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 6.0 \text{ V}$	50	120	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2	V
Small Signal Characteristics					
f_T	Current Gain - Bandwidth Product	$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$	450		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		0.6	pF
τ_b/C_c	Collector Base Time Constant	$I_C = 5.0 \text{ mA}, V_{CB} = 10 \text{ V}, f = 79.8 \text{ MHz}$		12	pS

* Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

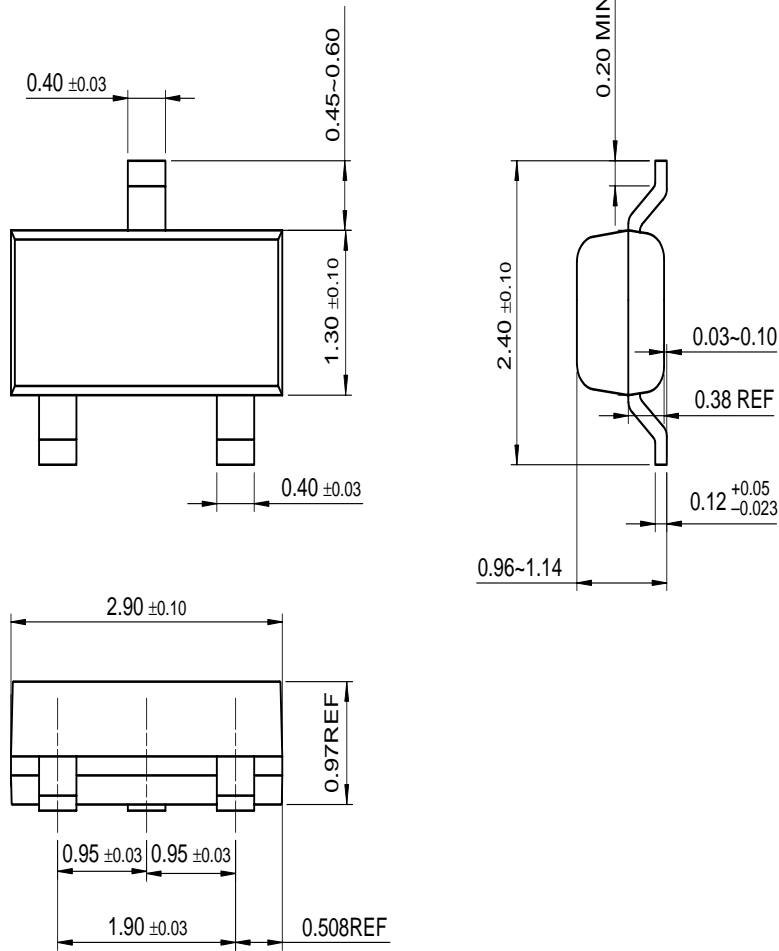
Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation	225	mW
	Derate above 25°C	1.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	$^\circ\text{C/W}$

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

Package Dimensions

SOT-23



Dimensions in Millimeters

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